#### STARC Aids your Design

### Design Methodology toward DFM

### STARCAD-21 overview

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## Industry Change in System LSI

Value up the design platform in System LSI as industry standard









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<3>

# Key issues in UDSM phenomena

### Timing, Signal Integrity, Reliability and Manufacturability are NOT independent but trade off





### Design methodology for production



## Main release schedule

Basic design methodology

RTLtoGDS2 basic design flow (V1.0 2004/4)

Standard design methodology

Huge design solution (Hierarchical, Flat) (V1.5 2004/10)

Low power design solution (V2.0 2005/4)

High effective design methodology (V2.5 2005/10, V3.0 2006/3)

Reduction of design turn around time

Reduction of design margin



## Features in V1.0

- Basic design methodology in 90nm technology
  - Design tool chain based on commercial EDA products
  - Integrated methodology for timing, SI and DFM closures
  - Higher efficiency in timing with pseudo hierarchical design
  - New design database recommended by EDA vendor
- Consistent EDA library specification with EDA tool
  Focusing on timing and SI
- Clear sign-off rule taken into account of process variation
  - Consideration of process variation without any penalty in timing closure
- Important tool evaluation for 90nm phenomena analysis
  Focusing on CTS, SI, LPE and EM

## Sign-off check flow





### Inserting double via as DFM



### Inserting dummy metal as DFM



## V1.5 Hierarchical design - Chip image -





### Features in V1.5

- Hierarchical design methodology to take true benefit
- Reduction for timing verification corners
- Definition for verification corners in cross talk noise, IR drop and signal EM
- SDC checker
- IP modeling specification in hierarchical design



## V2.0 Low power design - Chip image -





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### Features in V2.0

Low power design

Design flow for multi power with power shut down operation

Design flow for multi Vth

Design rule check for multi power (Ex. Power island, Level shifter insertion)

Cross talk analysis in multi power (among different powers)

- Multi power supply voltage libraries
  - 1.2V and 1.0V
  - Delay calculation and noise analysis
- Gated clock with cloning and decloning

CTS in multi power



### Features in V2.0

- V variable library in each supply voltage (Single library and accurate interpolate tool)
- Considerations of IR drop at each instance
- Power analysis with switching toggle
- Power line noise analysis
- Effective max capacitance and max transition constraints handling
- Integration with SDC checker and SDC generator
- Reduction in pessimistic cross talk noise by noise immunity
- Avoidance in signal EM
- Enhancement in inserting dummy metal with less impact in timing and SI



## Multi voltage libraries

#### Specification of multi voltage

		Temperature		
	base	variation	IR-Drop	[°C]
High Voltage	1.2	±0.1	- 0.1	- 40 <b>~</b> 125
Low Voltage	1.0	$\pm 0.05$	- 0.1	- 40 <b>~</b> 125

#### Characterize conditions

Process		MAX(SS)		TYP(TT)	MIN(FF)	
	Temp.	-40	125	25	-40	125
H-Vdd(1.2v)		1.1V	1.1V	1.2V	1.3V	1.3V
	IR-Drop(-0.1v)	1.0V	1.0V		1.2V	1.2V
L-Vdd(1.0v)		0.95V	0.95V	1.0V	1.05V	1.05V
	IR-Drop(-0.1v)	0.85V	0.85V		0.95V	0.95V
Process		MAX(SS)		TYP(TT)	MIN(FF)	
	Temp.	-40	125	25	-40	125
I/O		1.1V	1.1V	1.2V	1.3V	1.3V
	Process	MAX(SS)		TYP(TT)	MIN(FF)	
	Temp.	-40	125	25	-40	125
Level shifter		1.1V	1.1V	1.2V	1.3V	1.3V
		\$	\$	\$	\$	\$
		0.95V	0.95V	1.0V	1.05V	1.05V



## Production flow for low power design



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<17>

### Power reduction by selecting Multi-Vth





### Effectiveness in low power design



# First silicon success!!

Methodology verification project(SH-4)





#### ZD flow

By using the STARCAD-21 which is fully integrated design methodology •Grantee a chip to work in production on the computer environment at design phase (Sign-off)

•Realize similar design turn around time in 90nm to 130nm (33% up in productivity)

•Complete solution in 90nm technology difficulty such as timing, signal integrity and design for manufacturing

### **De-facto standard in SOC design methodology**

# Beyond V2.0

Reducing design turn around time drastically Enhance for timing constraints handling Multi corners, Multi scenario Golden timing constraint flow Reducing sign-off corners Timing and SI Good hand-off criteria Hierarchical sign-off Less design margin On-chip variation Considerations instance base IR-drop more effectively Tool accuracies

65nm design methodology with DFM



### Importance for DFM design factor in 65nm Comparing with 90nm



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<22>

# Verification with OCV (On-Chip-Variation)

#### What is OCV?

- Process variation
- Incompleteness on OPC (Optical Proximity Correction)
- Hard consideration in design
  - Temperature in chip
  - Instance base IR drop
- Other design margins
- Tool accuracy

#### Current verification

- Verification corner
  - In order to guarantee chip operation several different sets in
  - P: Process (Transistor process )
  - W: Wire (Wire process)
  - V: Voltage (Supply voltage) and
  - T: Temperature
- Verifying at each verification corner with OCV for mainly timing

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### No methodology to define OCV value!!



<23>

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# Variation in process and design



# Difficulty in timing closure with OCV



## Summary

- STARCAD-21 is the state of the art design methodology for 90nm and below system LSI
- STARCD-21 is developed by collection of talent and experience in the Japanese semiconductor industry
- **STARCAD-21** is applicable to real system LSI now
- STARCAD-21 is the de-facto standard design methodology
- STARCD-21 is expanding to support DFM

